

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

S2000N

COLOR TV HORIZONTAL OUTPUT APPLICATIONS

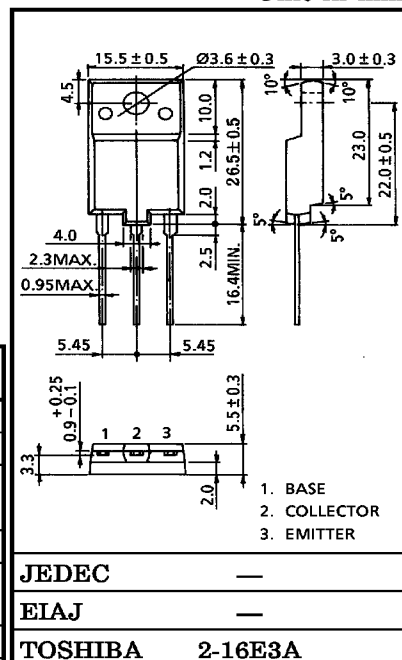
COLOR TV SWITCHING REGULATOR APPLICATIONS

- High Voltage : $V_{CES} = 1500\text{ V}$
- High Speed : $t_f = 0.7\text{ }\mu\text{s}$ (Max.)
- Low Saturation Voltage : $V_{CE(sat)} = 5\text{ V}$ (Max.)
- Collector Metal (Fin) is Fully Covered with Mold Resin.
(IS) Package

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CES}	1500	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	8	A
	Pulse	I_{CP}	15	
Base Current		I_B	4	A
Collector Power Dissipation ($T_c = 25^\circ\text{C}$)		P_C	50	W
Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	$-55 \sim 150$	$^\circ\text{C}$
Thermal Resistance		$R_{th(j-c)}$	2.5	$^\circ\text{C/W}$

Unit in mm

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

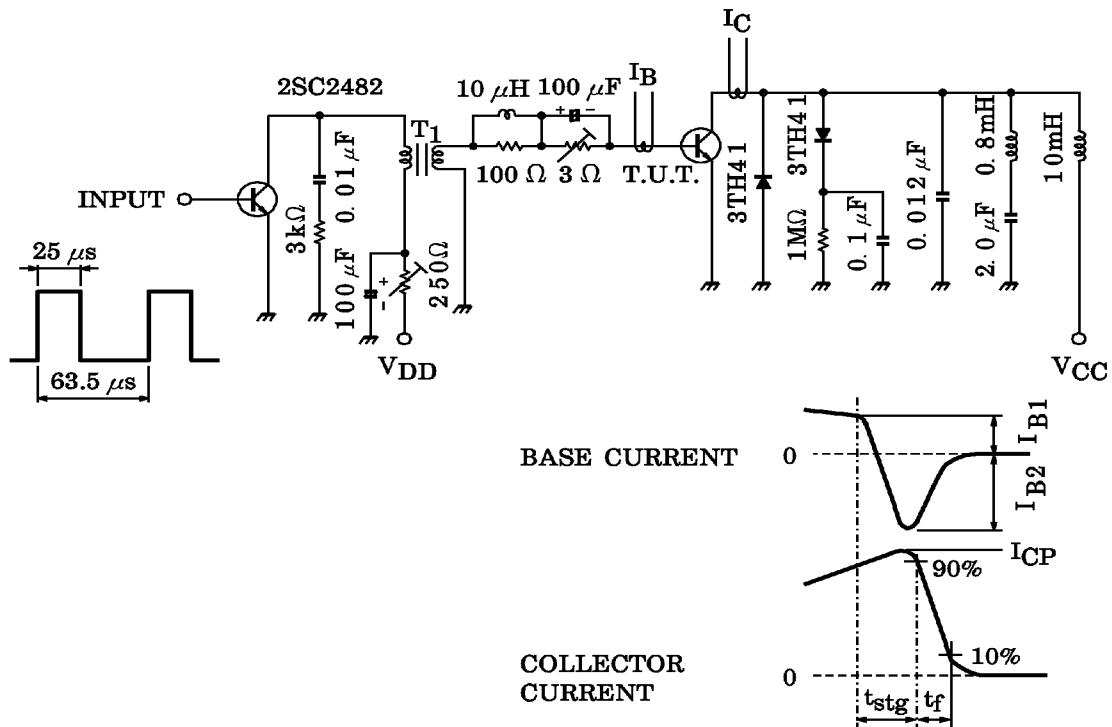
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 1500\text{ V}, V_{BE} = 0$	—	—	1	mA
Emitter-Base Breakdown Voltage	V_{EBO}	$I_E = 1\text{ mA}, I_C = 0$	5	—	—	V
DC Current Gain	$h_{FE}(1)$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	10	—	30	
	$h_{FE}(2)$	$V_{CE} = 5\text{ V}, I_C = 4.5\text{ A}$	4.5	—	9	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 4.5\text{ A}, I_B = 2\text{ A}$	—	—	1	V
		$I_C = 4.5\text{ A}, I_B = 1\text{ A}$	—	—	5	
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 4.5\text{ A}, I_B = 1\text{ A}$	—	0.9	1.2	V
Collector-Emitter Sustain Voltage	$V_{CEX(sus)}$	$L = 40\text{ mH}, I_B = 500\text{ mA}$ $V_{BE} = -1.7\text{ V}$	700	—	—	V
Transition Frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	95	—	pF
Switching Time (Fig.1)	Storage Time t_{stg}	$I_{CP} = 4.5\text{ A}, I_{B1}(\text{end}) = 1\text{ A}$ $f_H = 15.75\text{ kHz}$	—	8	12	μs
	Fall Time t_f		—	0.4	0.7	

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Fig.1 SWITCHING TIME TEST CIRCUIT



Base Current Gradient

$$dI_B / dt = \frac{I_{B1} + I_{B2}}{t_{stg}} \text{ (A / } \mu\text{s)}$$

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